

CMLDM3757**SURFACE MOUNT SILICON
N-CHANNEL AND P-CHANNEL
ENHANCEMENT-MODE
COMPLEMENTARY MOSFET****SOT-563 CASE****APPLICATIONS:**

- Load/Power switches
- Power supply converter circuits
- Battery powered portable devices

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Drain-Source Voltage

Gate-Source Voltage

Continuous Drain Current (Steady State)

Maximum Pulsed Drain Current ($t_p=10\mu\text{s}$)

Power Dissipation (Note 1)

Power Dissipation (Note 2)

Power Dissipation (Note 3)

Operating and Storage Junction Temperature

Thermal Resistance (Note 1)

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$)

SYMBOL	TEST CONDITIONS	N-CH (Q1)			P-CH (Q2)			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
I_{GSS}, I_{GSSR}	$V_{GS}=4.5\text{V}, V_{DS}=0$	-	-	5.0	-	-	2.0	μA
I_{DSS}	$V_{DS}=16\text{V}, V_{GS}=0$	-	-	1.0	-	-	1.0	μA
BV_{DSS}	$V_{GS}=0, I_D=250\mu\text{A}$	20	-	-	20	-	-	V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.45	-	1.0	0.45	-	1.0	V
V_{SD}	$V_{GS}=0, I_S=350\text{mA}$	-	-	1.2	-	-	1.2	V
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=540\text{mA}$	-	0.35	0.55	-	-	-	Ω
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=430\text{mA}$	-	-	-	-	0.4	0.9	Ω
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=500\text{mA}$	-	0.5	0.7	-	-	-	Ω
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=300\text{mA}$	-	-	-	-	0.55	1.2	Ω
$r_{DS(ON)}$	$V_{GS}=1.8\text{V}, I_D=350\text{mA}$	-	0.7	0.9	-	-	-	Ω
$r_{DS(ON)}$	$V_{GS}=1.8\text{V}, I_D=150\text{mA}$	-	-	-	-	0.75	2.0	Ω

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm^2 (2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm^2 (3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm^2 www.centrasemi.com**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMLDM3757 consists of complementary silicon N-Channel and P-Channel enhancement-mode MOSFETs designed for high speed pulsed amplifier and driver applications. These MOSFETs offer very low $r_{DS(ON)}$ and low threshold voltage.

MARKING CODE: 3C7**FEATURES:**

- ESD protection up to 1800V (Human Body Model)
- 350mW power dissipation
- Very low $r_{DS(ON)}$
- Low threshold voltage
- Logic level compatible
- Small, SOT-563 surface mount package

SYMBOL	N-CH (Q1)	P-CH (Q2)	UNITS
V_{DS}	20		V
V_{GS}	8.0		V
I_D	540	430	mA
I_{DM}	1500	750	mA
P_D	350		mW
P_D	300		mW
P_D	150		mW
T_J, T_{stg}	-65 to +150		$^{\circ}\text{C}$
Θ_{JA}	357		$^{\circ}\text{C/W}$

R6 (8-June 2015)

CMLDM3757

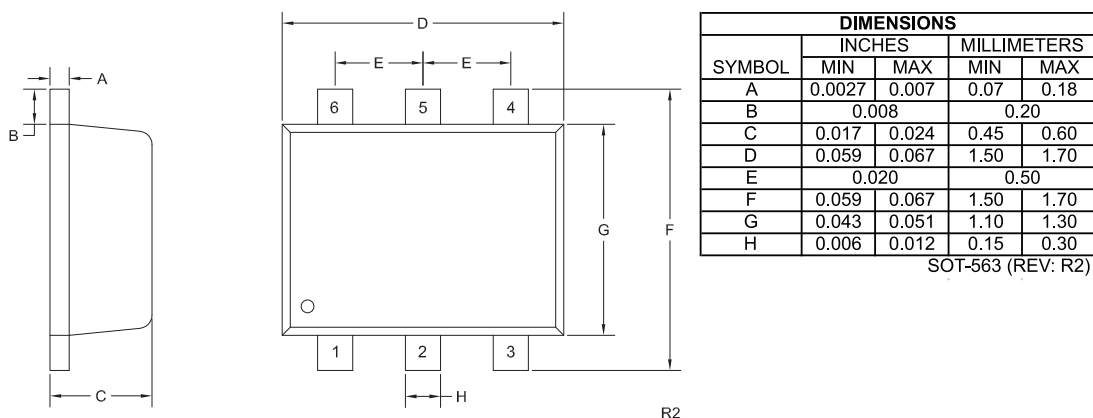
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COMPLEMENTARY MOSFETS**



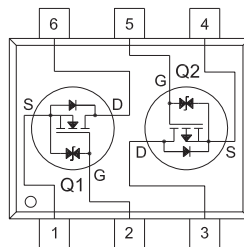
ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	N-CH (Q1)		P-CH (Q2)		UNITS
		TYP	MAX	TYP	MAX	
C_{rss}	$V_{DS}=16\text{V}, V_{GS}=0, f=1.0\text{MHz}$	-	20	-	20	pF
C_{iss}	$V_{DS}=16\text{V}, V_{GS}=0, f=1.0\text{MHz}$	-	150	-	175	pF
C_{oss}	$V_{DS}=16\text{V}, V_{GS}=0, f=1.0\text{MHz}$	-	25	-	30	pF
$Q_{g(\text{tot})}$	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=500\text{mA}$	1.58	-	-	-	nC
$Q_{g(\text{tot})}$	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}$	-	-	1.2	-	nC
Q_{gs}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=500\text{mA}$	0.17	-	-	-	nC
Q_{gs}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}$	-	-	0.24	-	nC
Q_{gd}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=500\text{mA}$	0.24	-	-	-	nC
Q_{gd}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}$	-	-	0.36	-	nC
t_{on}	$V_{DD}=10\text{V}, V_{GS}=4.5\text{V}, I_D=540\text{mA}, R_G=10\Omega$	10	-	-	-	ns
t_{off}	$V_{DD}=10\text{V}, V_{GS}=4.5\text{V}, I_D=540\text{mA}, R_G=10\Omega$	25	-	-	-	ns
t_{on}	$V_{DD}=10\text{V}, V_{GS}=4.5\text{V}, I_D=215\text{mA}, R_G=10\Omega$	-	-	38	-	ns
t_{off}	$V_{DD}=10\text{V}, V_{GS}=4.5\text{V}, I_D=215\text{mA}, R_G=10\Omega$	-	-	48	-	ns

SOT-563 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) Source Q1
- 2) Gate Q1
- 3) Drain Q2
- 4) Source Q2
- 5) Gate Q2
- 6) Drain Q1

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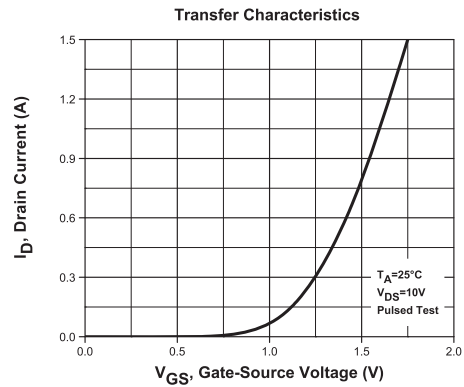
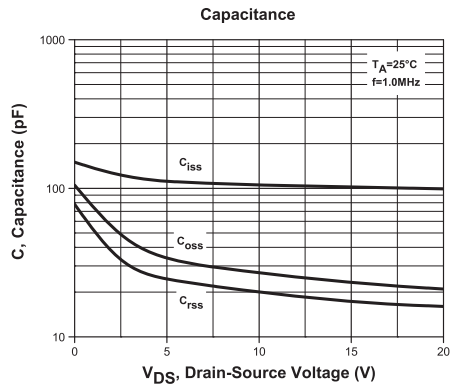
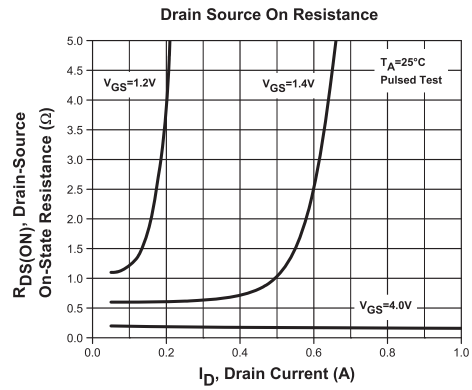
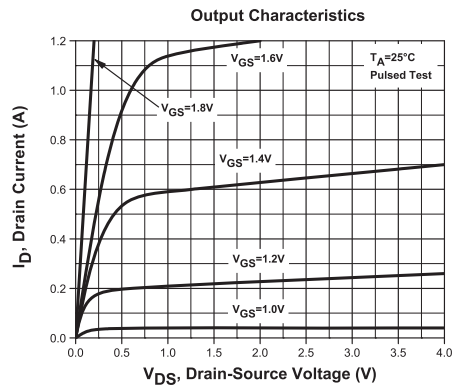
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N-CHANNEL TYPICAL ELECTRICAL CHARACTERISTICS



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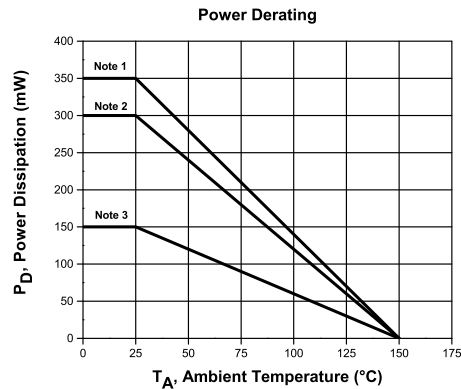
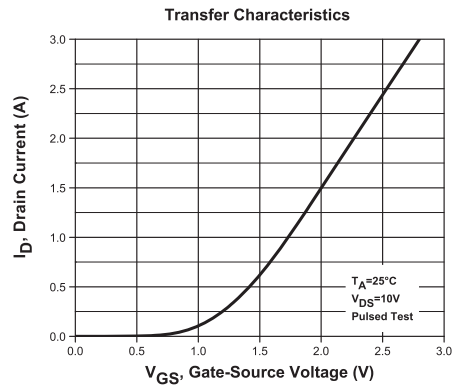
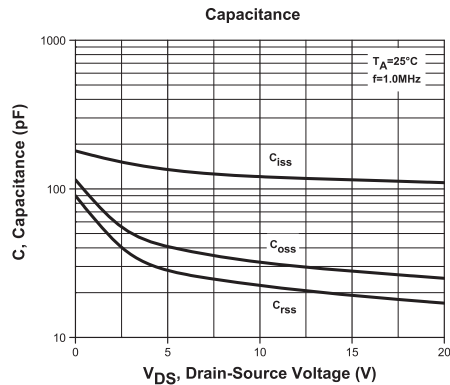
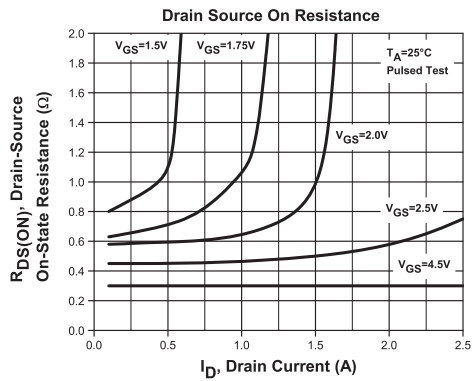
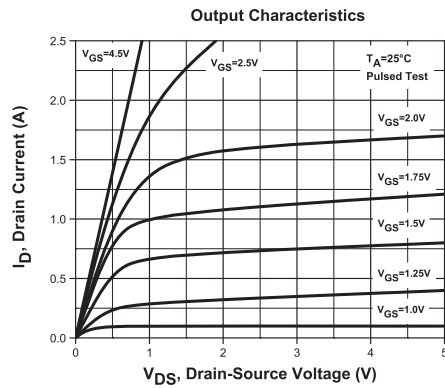
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P-CHANNEL TYPICAL ELECTRICAL CHARACTERISTICS



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OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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